



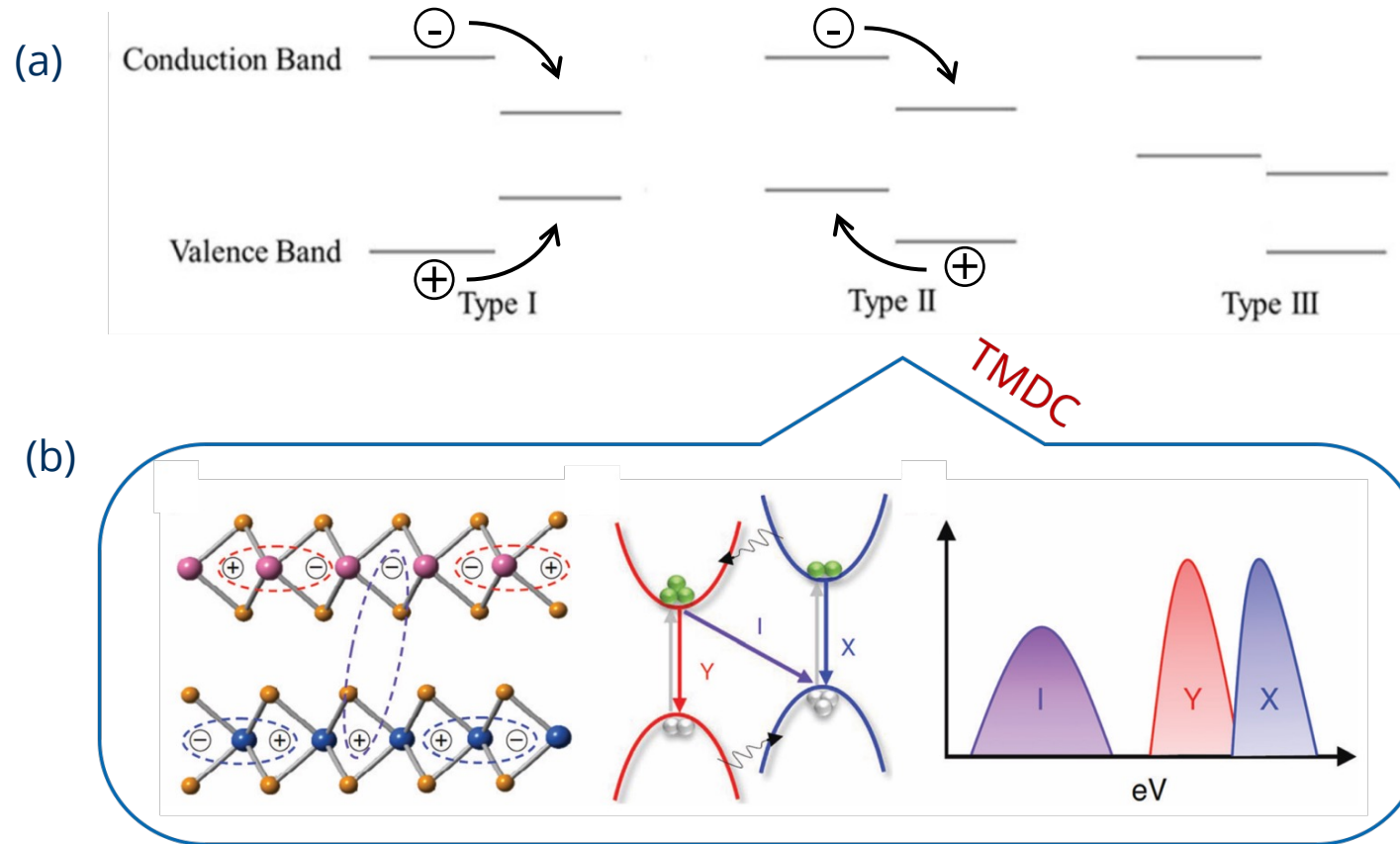
Wei Li, Gautam Jha, Thomas Brumme, Thomas Heine

Chair of Theoretical Chemistry, TU Dresden

Modulation of optical selection rules in twisted transition metal dichalcogenide heterobilayer

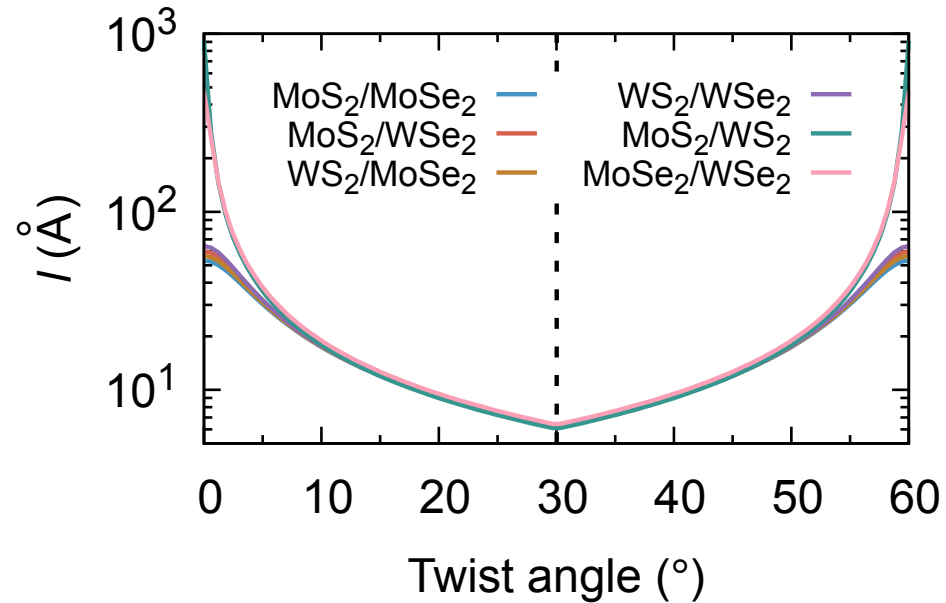
Mar 06, 2024 // Minneapolis

Why TMDC heterostructures?



(a) Different types of vdWH band structures.^[1] (b) Excitonic behavior in Type-II alignment vdWH.^[2]

How: Multiscale approach



- Geometry optimization performed by Force-Field^{[1][2]}
- Electronic properties calculated by DFTB^[3]

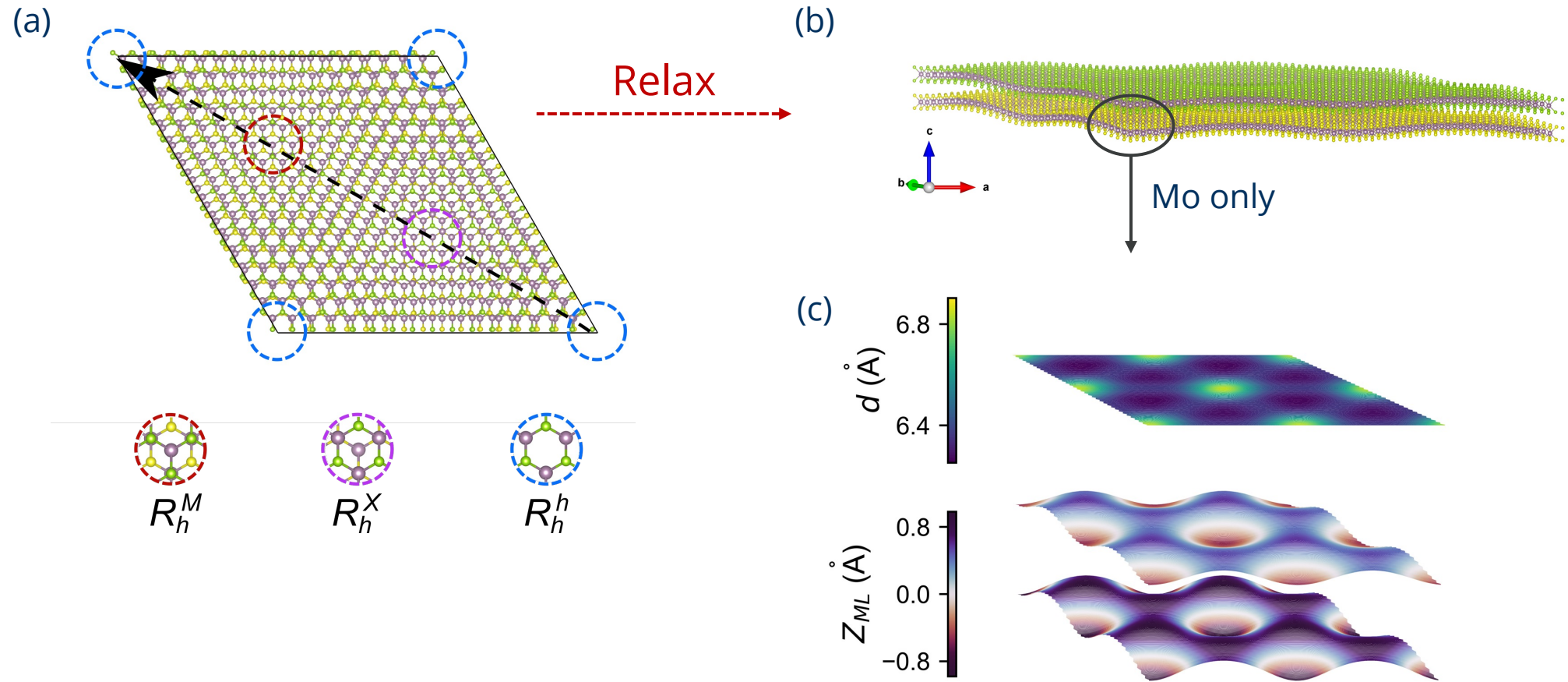
- Lattice size: $10^1 - 10^3$ Å
- Number of atoms: 50 – 5×10^5

[1] *J. Appl. Phys.* **2013**, 114, 064307.

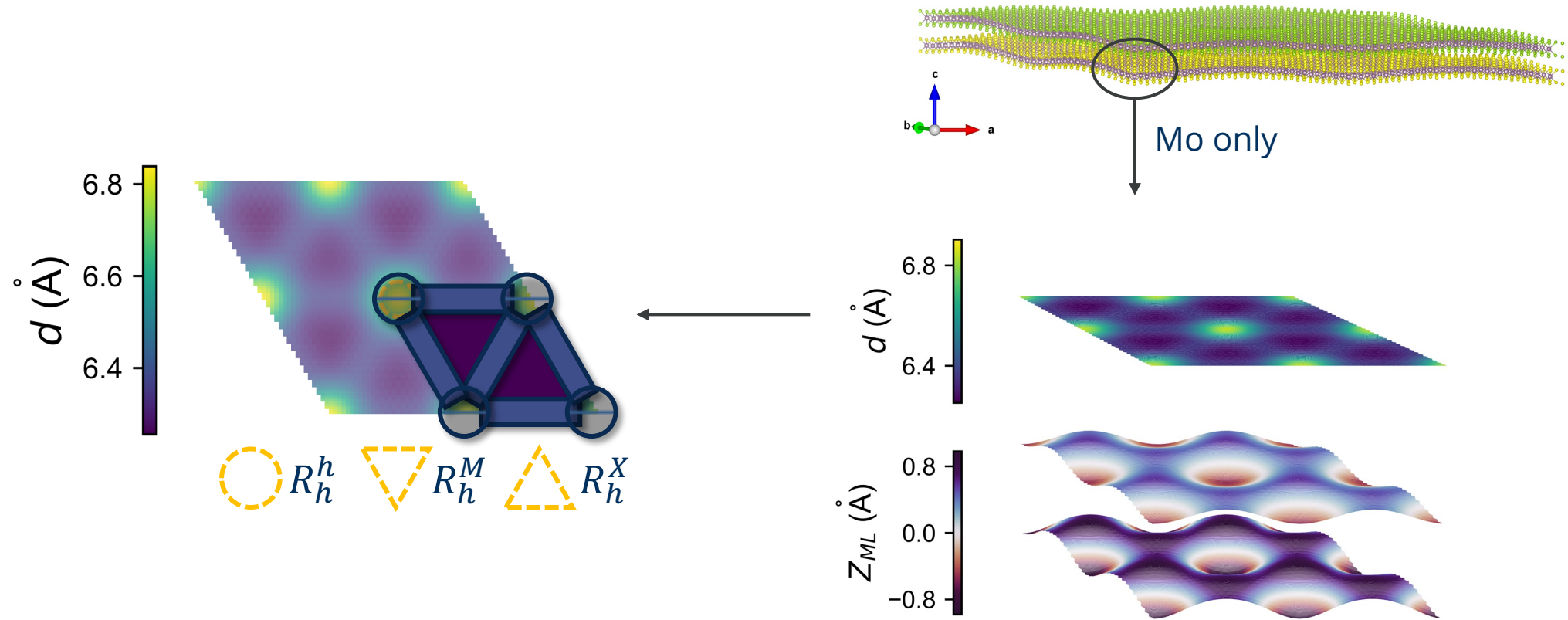
[2] *J. Phys. Chem. C* **2019**, 123, 9770.

[3] *J. Chem. Theory Comput.* **2022**, 18, 4472.

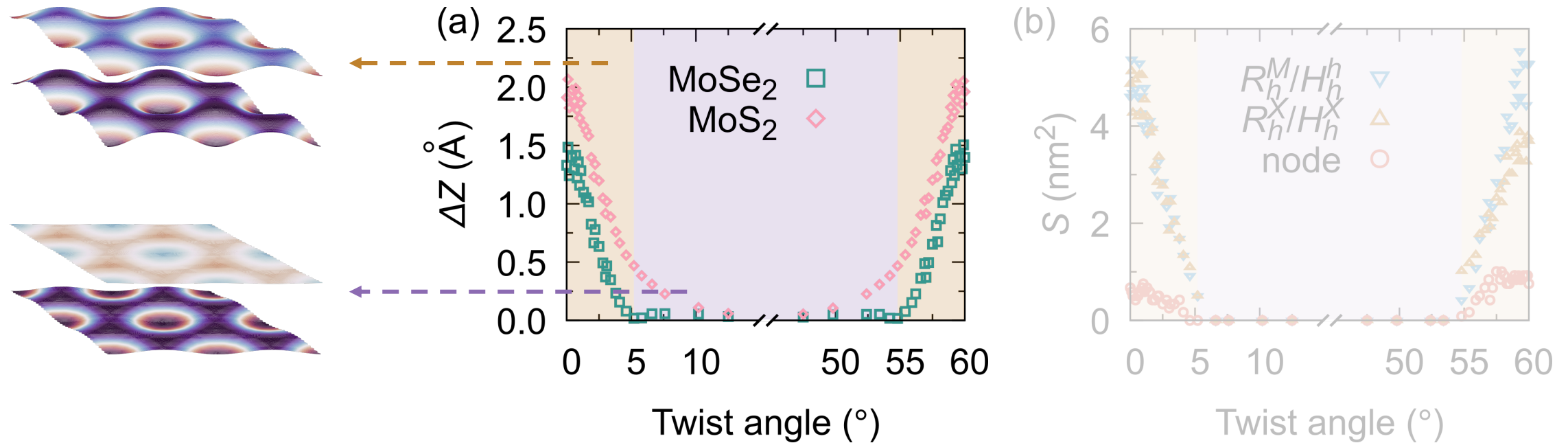
R-type stackings – MoS₂/MoSe₂ at 0°



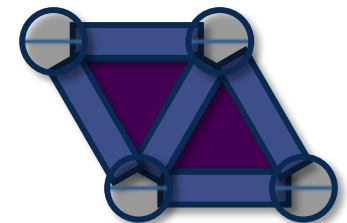
R-type stackings – MoS₂/MoSe₂ at 0°



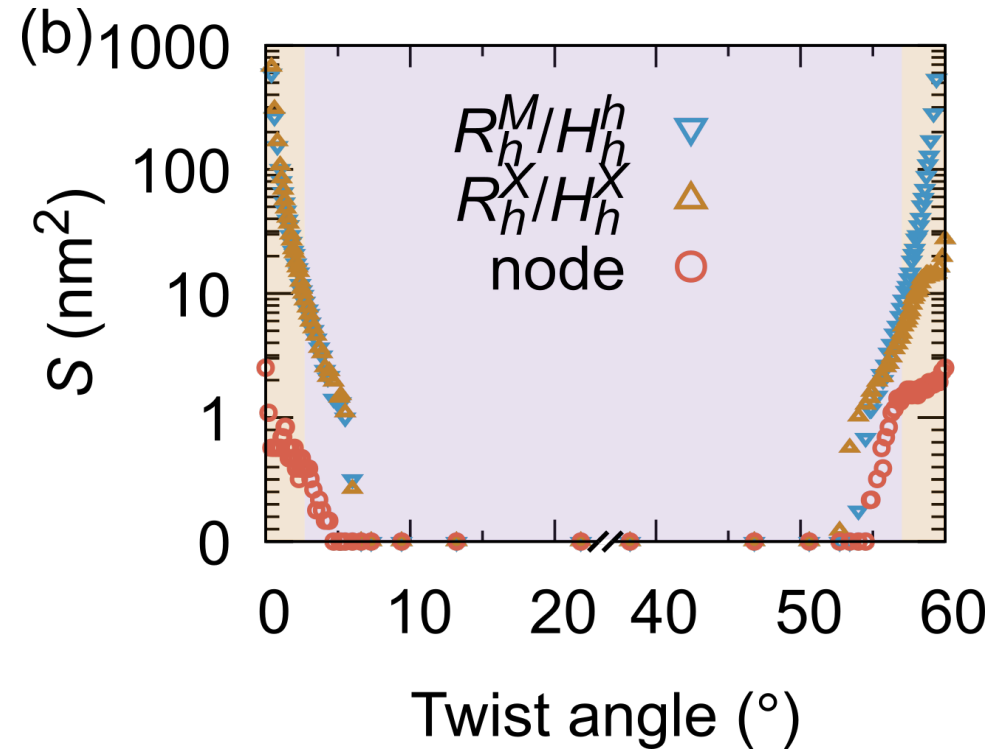
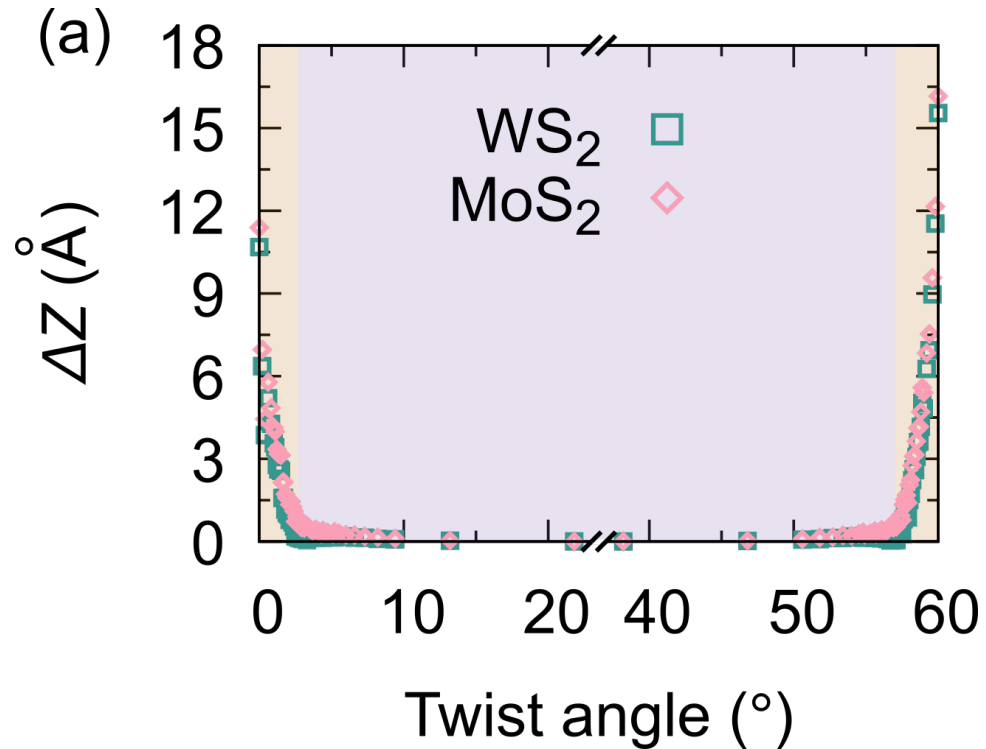
MoS₂/MoSe₂ at different twist angles



(a) Magnitude of corrugation of each layer. (b) Area of domains and node

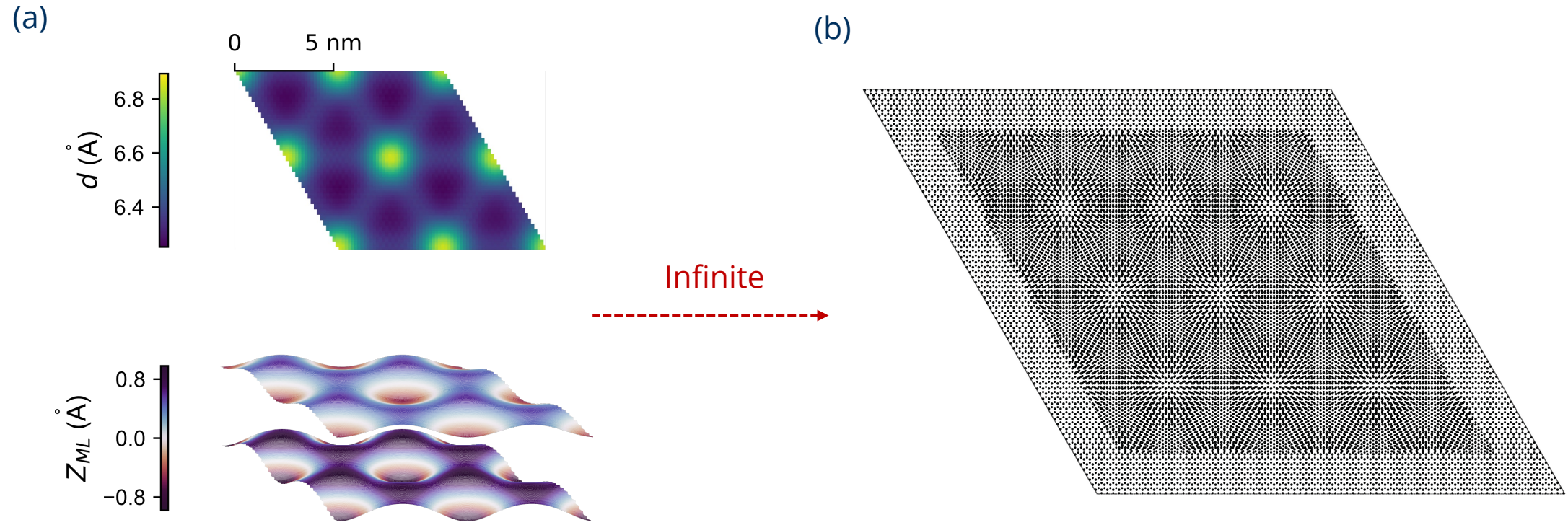


MoS₂/WS₂ at different twist angles

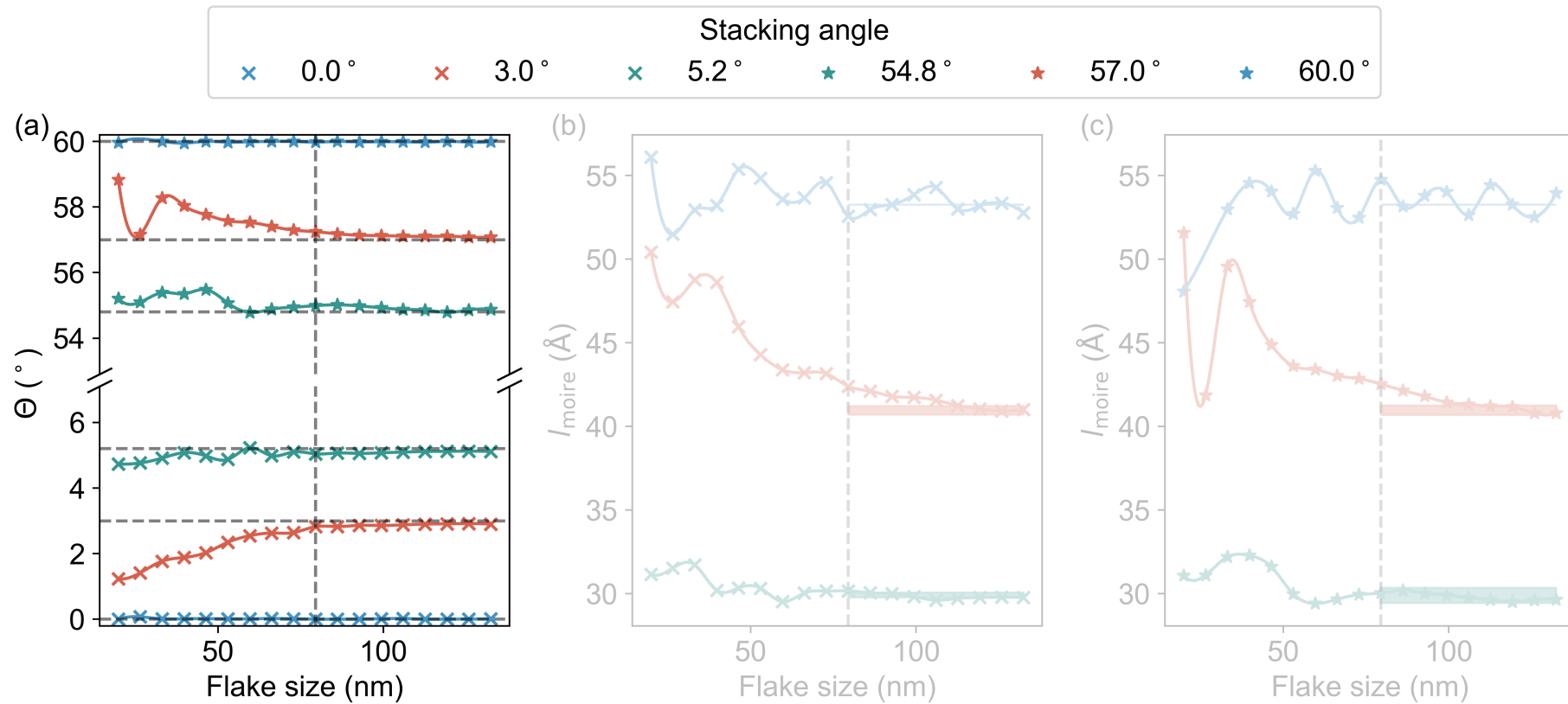


(a) Magnitude of corrugation of each layer. (b) Area of domains and node

Theory vs experiment

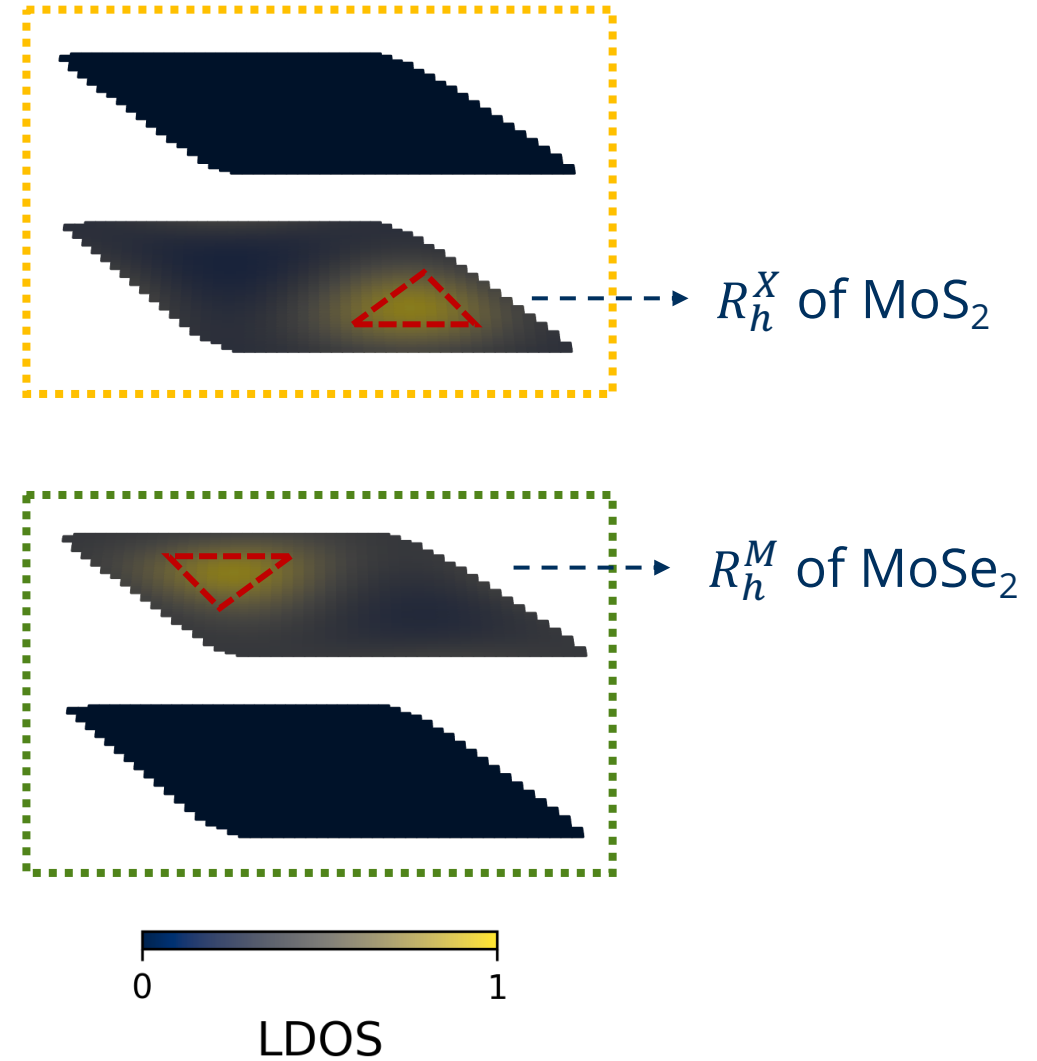
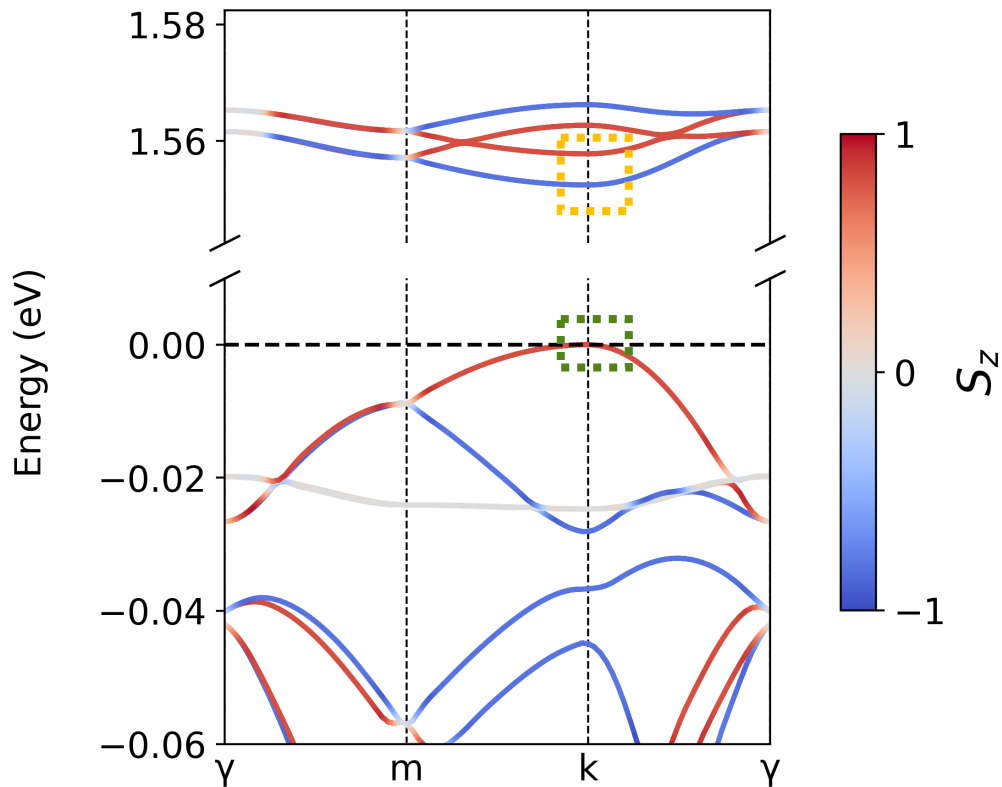


MoS₂/MoSe₂ flake systems

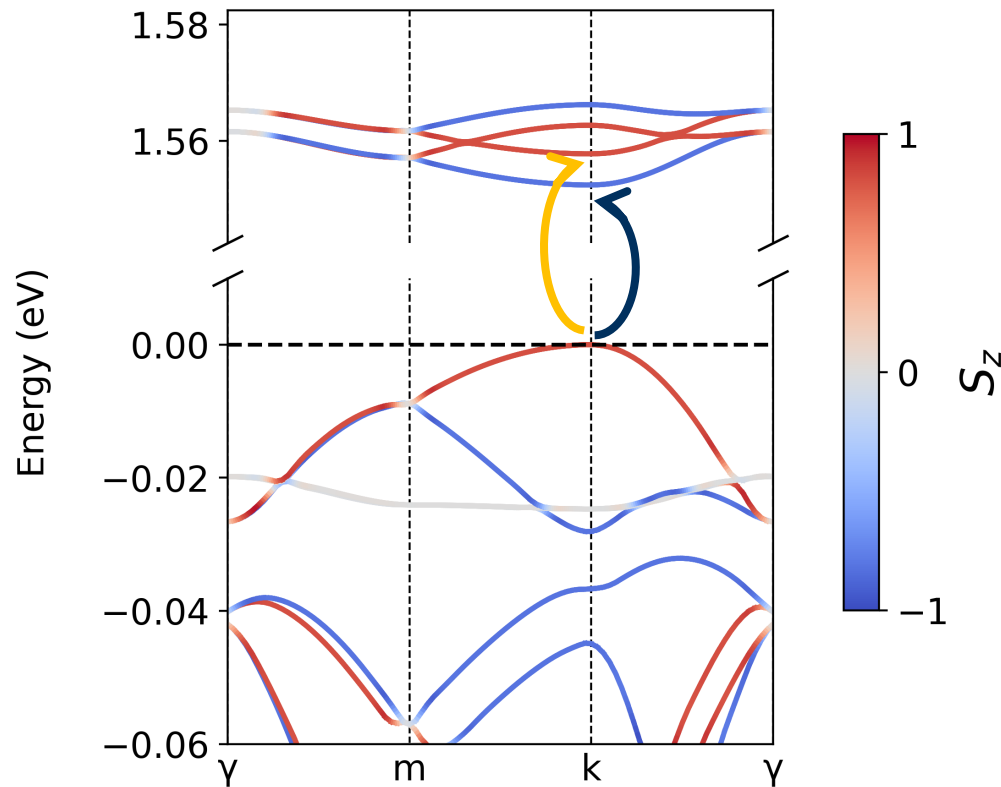


The effects of flake size on (a) twist angles and (b,c) moiré superlattice constant upon relaxation

MoS₂/WS₂ at 3° : Spin, angular momentum and g-factors

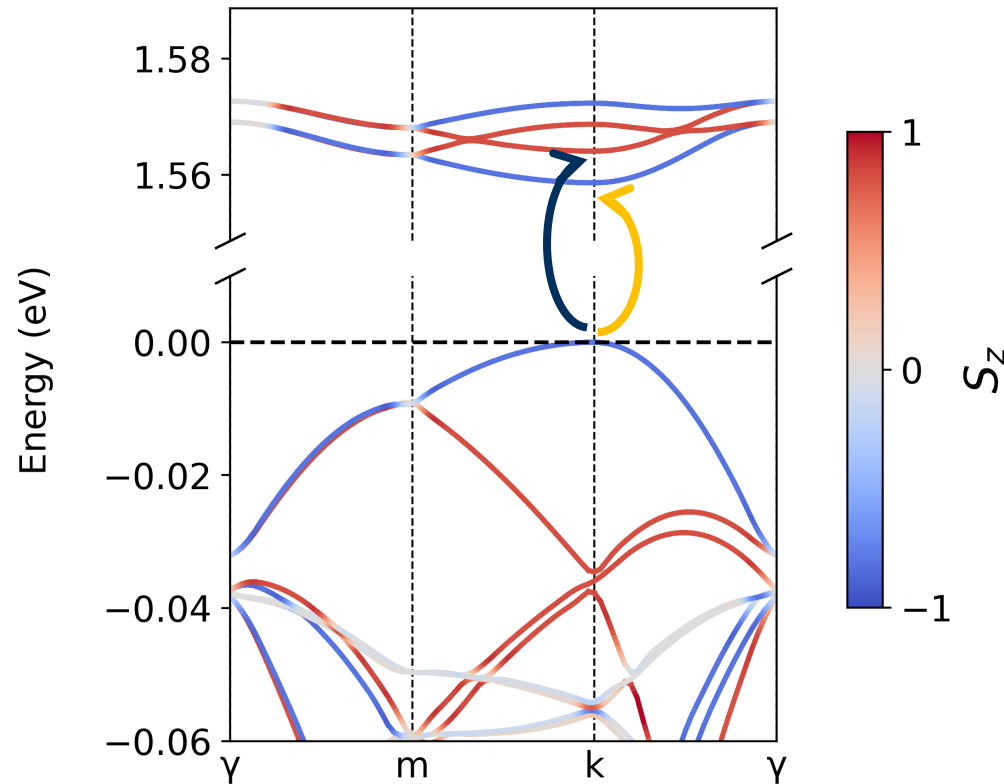


MoS₂/WS₂ at 3° : Spin, angular momentum and g-factors



R-type stacking		
g^{HS}	-1.2	2.78
transition	$v \rightarrow c$	$v \rightarrow c+1$
spin	$\uparrow\downarrow$	$\uparrow\uparrow$
ΔL	1.39	1.39

MoS₂/WS₂ at 57° : Spin, angular momentum and g-factors



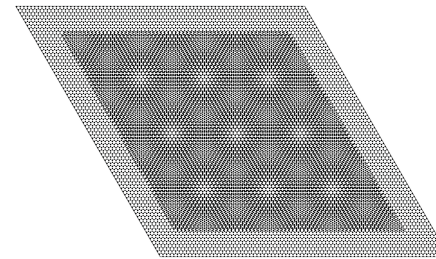
H-type stacking		
g^{HS}	-2.28	1.7
transition	$v \rightarrow c$	$v \rightarrow c+1$
spin	$\uparrow\downarrow$	$\uparrow\uparrow$
ΔL	-1.14	-1.14

Summary

- Significant lattice reconstruction
 - Domain formation
- Out-of-plane corrugation



- Commensurate vs incommensurate model



- Spin orbital coupling effect and exciton g-factor

Acknowledgement



- Dr. Gautam Jha
- Dr. Thomas Brumme
- Prof. Dr. Thomas Heine

**TECHNISCHE
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DRESDEN**

2-EXCITING



**2-exciting**

**Developing optoelectronics in
two-dimensional semiconductors**
MSCA ITN (GA 956813)

**MARIE CURIE ACTIONS**

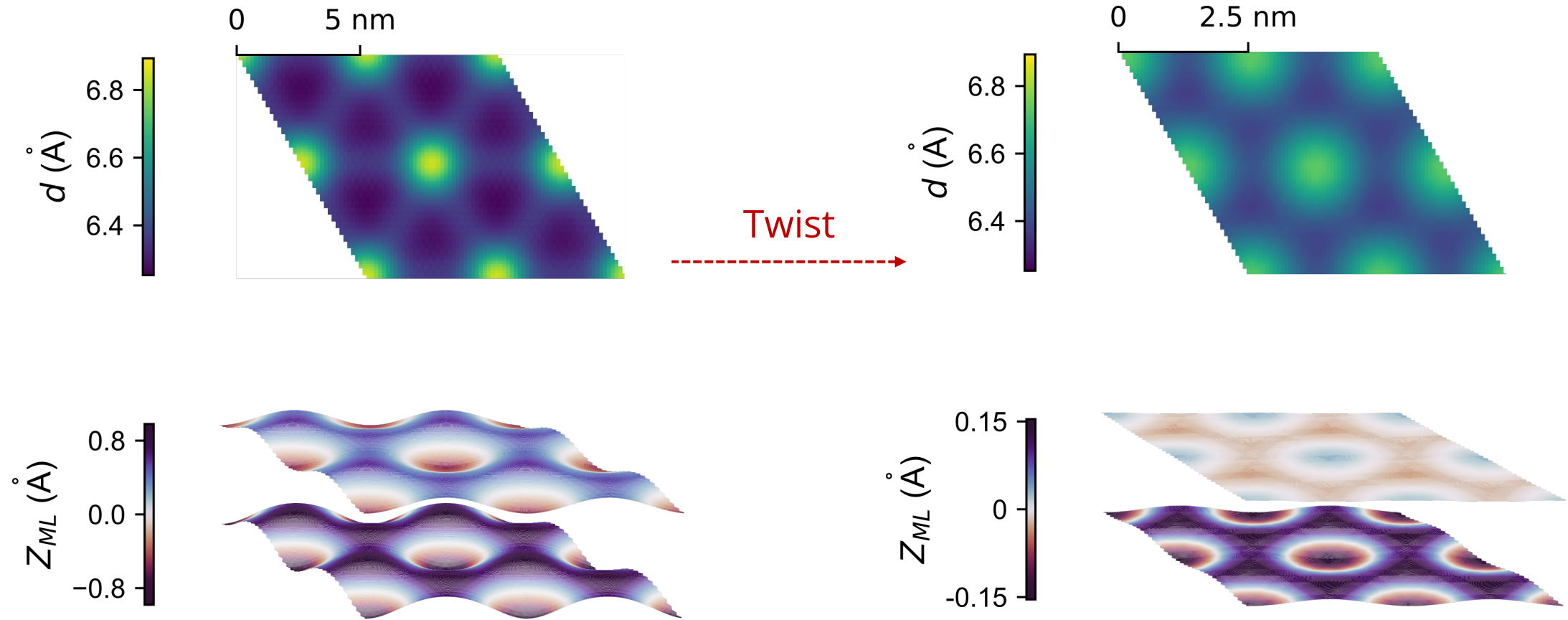
**European
Commission**

**Horizon 2020
European Union funding
for Research & Innovation**

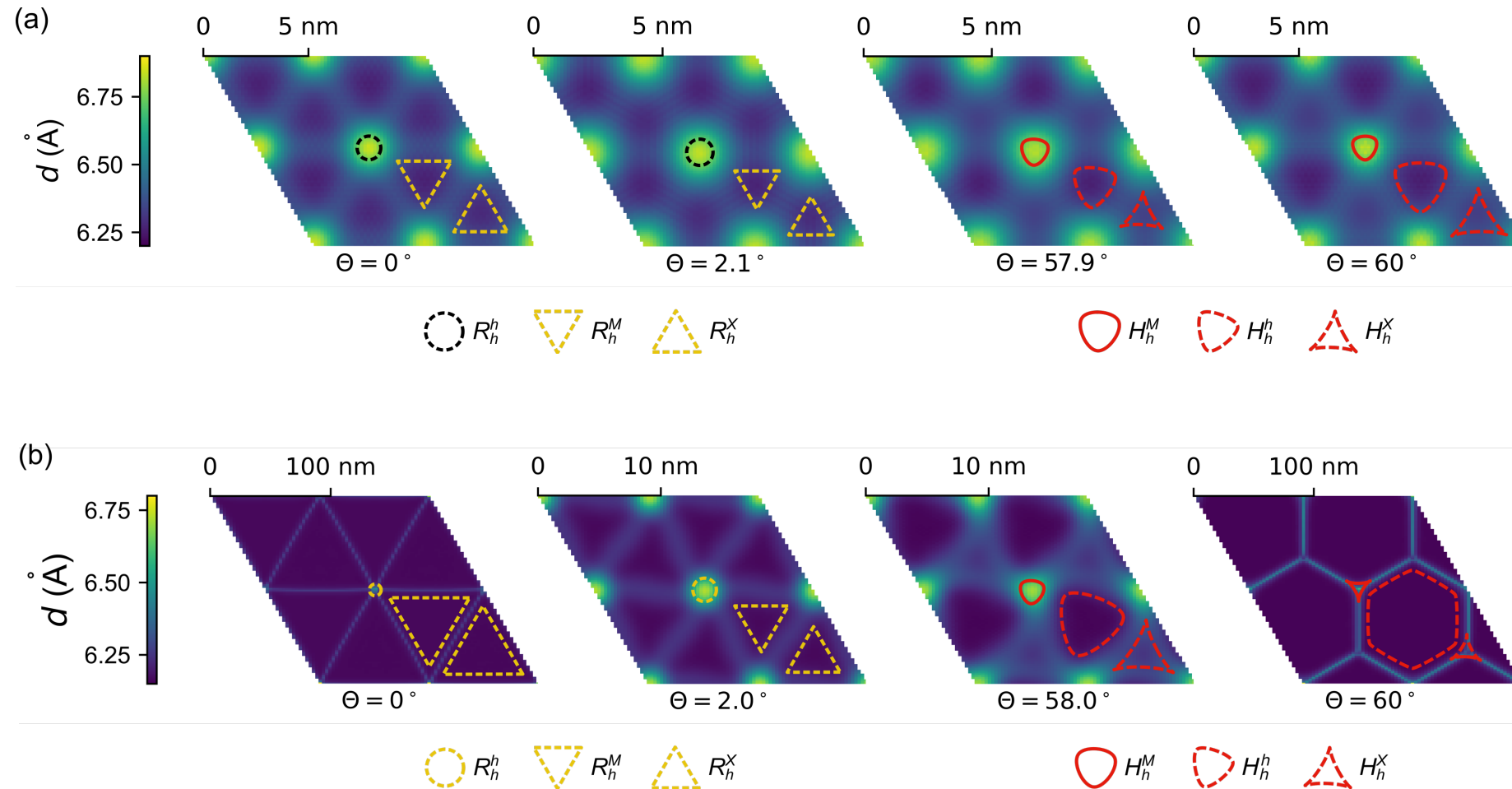


THANK YOU

R-type stackings – Relaxed $\text{MoS}_2/\text{MoSe}_2$ at 0° and 6.6°



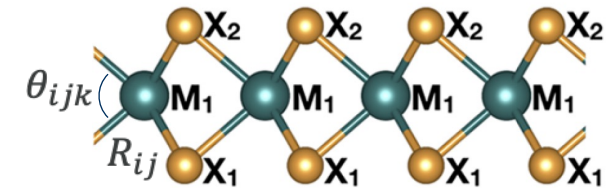
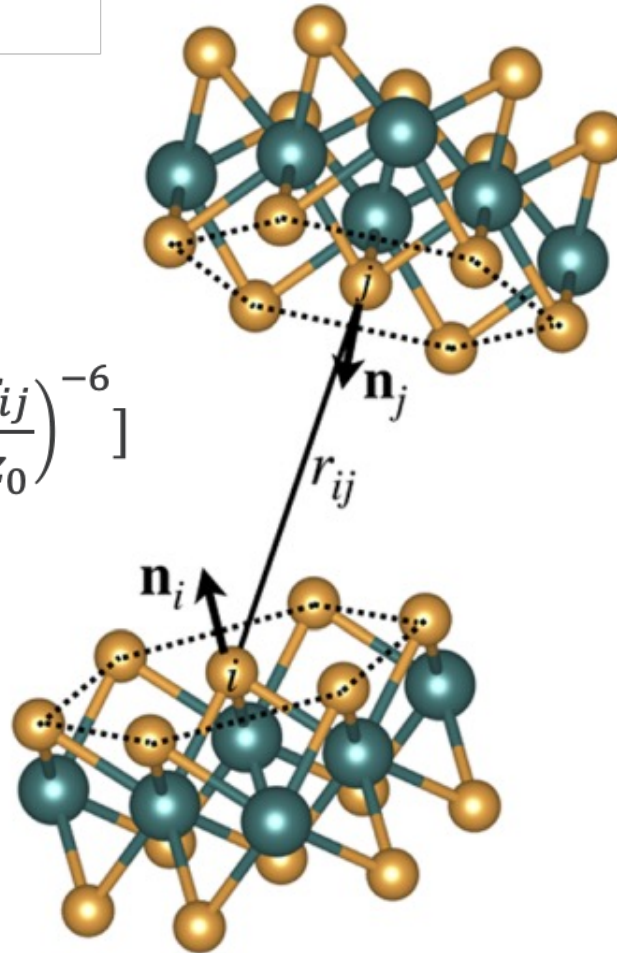
Backup: MoS₂/MoSe₂ and MoS₂/WS₂ at small twist angles



Backup: Force-field method

$$\frac{1}{2} \sum_i \sum_{j \neq i} [e^{-\lambda(r_{ij}-z_0)} V_\rho - A \left(\frac{r_{ij}}{z_0} \right)^{-6}]$$

Interlayer



$$\sum_i \sum_{j>i} \phi_2(R_{ij}) + \sum_i \sum_{j \neq i} \sum_{k>j} \phi_3(R_{ij}, R_{ik}, \theta_{ijk})$$

bond stretching + angle bending

Intralayer

Backup: DFTB

$$E_{\text{DFT}}[\rho] = T_S[\rho] + \int d\mathbf{r} v_{\text{ext}}(\mathbf{r})\rho(\mathbf{r}) + E_{\text{H}}[\rho] + E_{\text{xc}}[\rho]$$

↓ expand at ρ_0

$$E_{\text{DFTB}}[\rho_0 + \delta\rho] = E^0[\rho_0] + E^1[\rho_0, \delta\rho] + E^2[\rho_0, (\delta\rho)^2] \\ + E^3[\rho_0, (\delta\rho)^3]$$

Backup: MoS₂/WS₂ at 2.5°

